

100Volt, 0.18 Ω , MEGA RAD HARD HEXFET

International Rectifier's RAD HARD technology HEXFETs demonstrate virtual immunity to SEE failure. Additionally, under **identical** pre- and post-radiation test conditions, International Rectifier's RAD HARD HEXFETs retain **identical** electrical specifications up to 1×10^6 Rads (Si) total dose. No compensation in gate drive circuitry is required. These devices are also capable of surviving transient ionization pulses as high as 1×10^{12} Rads (Si)/Sec, and return to normal operation within a few microseconds. Since the RAD HARD process utilizes International Rectifier's patented HEXFET technology, the user can expect the highest quality and reliability in the industry.

RAD HARD HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits in space and weapons environments.

Product Summary

Part Number	BV _{DSS}	R _{DS(on)}	I _D
IRHY7130CM	100V	0.18 Ω	14.4A
IRHY8130CM	100V	0.18 Ω	14.4A

Features:

- Radiation Hardened up to 1×10^6 Rads (Si)
- Single Event Burnout (SEB) Hardened
- Single Event Gate Rupture (SEGR) Hardened
- Gamma Dot (Flash X-Ray) Hardened
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Avalanche Energy Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets

Absolute Maximum Ratings

Pre-Radiation

	Parameter	IRHY7130CM, IRHY8130CM	Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	14.4	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	9.1	
I _{DM}	Pulsed Drain Current ①	58	
P _D @ T _C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/K ⑤
V _{GS}	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	150	mJ
dv/dt	Peak Diode Recovery dv/dt ③	6.0	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature 300 (0.063 in. (1.6mm) from case for 10s)		
	Weight	7.0(typical)	g

Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0\text{ V}$, $I_D = 1.0\text{ mA}$
$\Delta BV_{DSS}/\Delta T_j$	Temperature Coefficient of Breakdown Voltage	—	0.11	—	$^\circ\text{V}/^\circ\text{C}$	Reference to 25°C , $I_D = 1.0\text{ mA}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.18	Ω	$V_{GS} = 12\text{ V}$, $I_D = 9.1\text{ A}$ ④
		—	—	0.20		$V_{GS} = 12\text{ V}$, $I_D = 14.4\text{ A}$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 1.0\text{ mA}$
g_{fs}	Forward Transconductance	2.5	—	—	S (⑦)	$V_{DS} > 15\text{ V}$, $I_{DS} = 14.4\text{ A}$ ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 0.8 \times \text{Max Rating}$, $V_{GS} = 0\text{ V}$
		—	—	250		$V_{DS} = 0.8 \times \text{Max Rating}$, $V_{GS} = 0\text{ V}$, $T_j = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20\text{ V}$
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -20\text{ V}$
Q_g	Total Gate Charge	—	—	50	nC	$V_{GS} = 12\text{ V}$, $I_D = 14.4\text{ A}$ $V_{DS} = \text{Max Rating} \times 0.5$
Q_{gs}	Gate-to-Source Charge	—	—	10		
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	20		
$t_{d(on)}$	Turn-On Delay Time	—	—	35	ns	$V_{DD} = 50\text{ V}$, $I_D = 14.4\text{ A}$, $R_G = 7.5\Omega$
t_r	Rise Time	—	—	75		
$t_{d(off)}$	Turn-Off Delay Time	—	—	70		
t_f	Fall Time	—	—	60		
L_D	Internal Drain Inductance	—	5.0	—	nH	Measured from drain lead, 6mm (0.25 in) from package to center of die.
L_S	Internal Source Inductance	—	15	—		Measured from source lead, 6mm (0.25 in) from package to source bonding pad.
C_{iss}	Input Capacitance	—	960	—	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$ $f = 1.0\text{ MHz}$
C_{oss}	Output Capacitance	—	340	—		
C_{rss}	Reverse Transfer Capacitance	—	85	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	14.4	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier.
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	58		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	$T_j = 25^\circ\text{C}$, $I_S = 14.4\text{ A}$, $V_{GS} = 0\text{ V}$ ④
t_{rr}	Reverse Recovery Time	—	—	275	ns	$T_j = 25^\circ\text{C}$, $I_F = 14.4\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$
Q_{RR}	Reverse Recovery Charge	—	—	2.5	μC	$V_{DD} \leq 50\text{ V}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	1.67	K/W ⑤	
R_{thJA}	Junction-to-Ambient	—	—	80		Typical socket mount

Radiation Performance of Rad Hard HEXFETs

International Rectifier Radiation Hardened HEXFETs are tested to verify their hardness capability. The hardness assurance program at International Rectifier uses two radiation environments.

Every manufacturing lot is tested in a low dose rate (total dose) environment per MIL-STD-750, test method 1019. International Rectifier has imposed a standard gate voltage of 12 volts per note 6 and a V_{DS} bias condition equal to 80% of the device rated voltage per note 7. Pre- and post-radiation limits of the devices irradiated to 1×10^5 Rads (Si) are identical and are presented in Table 1, column 1, IRHY7130CM. The values in Table 1 will be met for either of the two low dose rate test circuits that are

used. Both pre- and post-radiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison. It should be noted that at a radiation level of 1×10^5 Rads (Si) no changes in limits are specified in DC parameters.

High dose rate testing may be done on a special request basis using a dose rate up to 1×10^{12} Rads (Si)/Sec.

International Rectifier radiation hardened HEXFETs have been characterized in neutron and heavy ion Single Event Effects (SEE) environments. Single Event Effects characterization is shown in Table 3.

Table 1. Low Dose Rate ⑥ ⑦

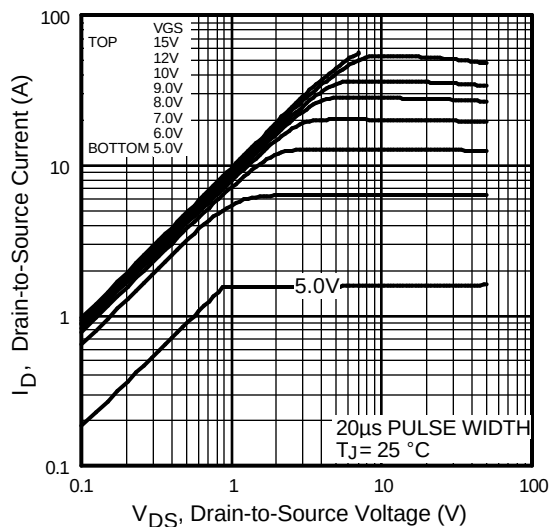
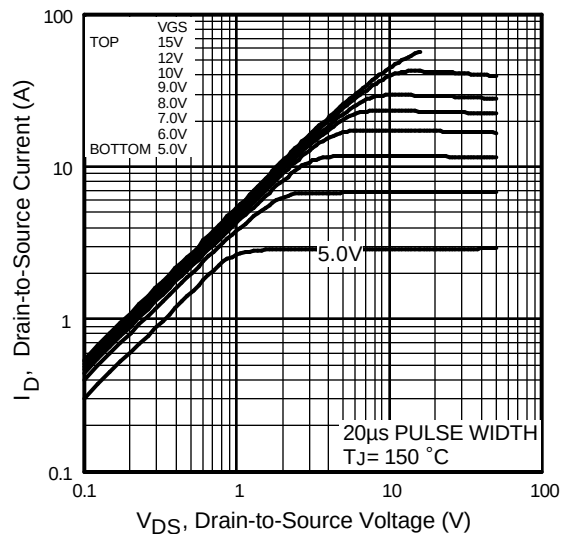
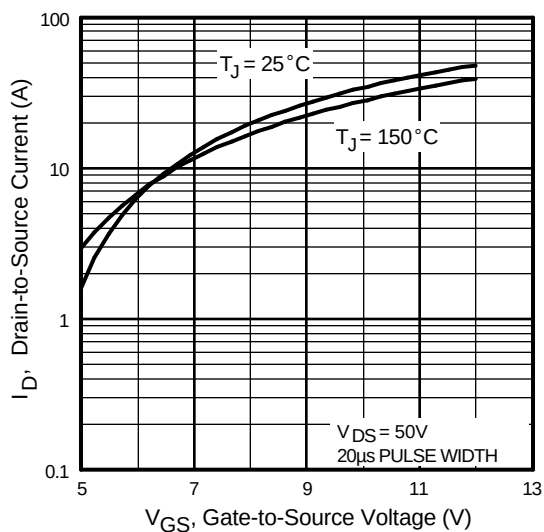
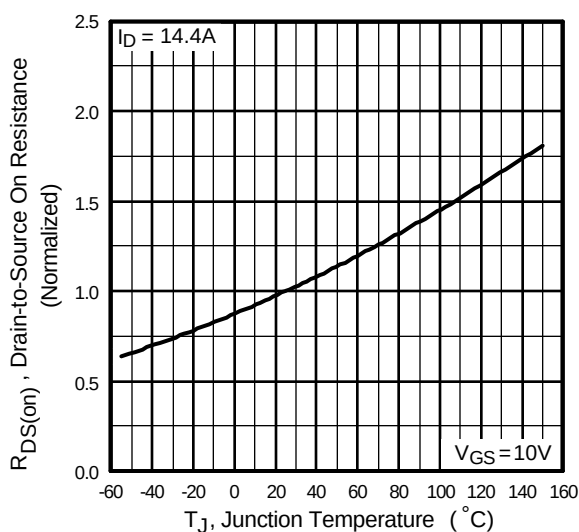
Table 1. Low Dose Rate ⑥ ⑦		IRHY7130CM		IRHY8130CM		Units	Test Conditions ⑩
	Parameter	100K Rads (Si)		1000K Rads (Si)			
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	100	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage ④	2.0	4.0	1.25	4.5		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	25	—	25	μA	V _{DS} =0.8 x Max Rating, V _{GS} =0V
R _{DS(on)1}	Static Drain-to-Source ④	—	0.18	—	0.24	Ω	V _{GS} = 12V, I _D = 9.1A
	On-State Resistance One						
V _{SD}	Diode Forward Voltage ④	—	1.8	—	1.8	V	T _C = 25°C, I _S = 14.4A, V _{GS} = 0V

Table 2. High Dose Rate ⑧

	Parameter	10^{11} Rads (Si)/sec			10^{12} Rads (Si)/sec			Units	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
V_{DSS}	Drain-to-Source Voltage	—	—	80	—	—	80	V	Applied drain-to-source voltage during gamma-dot
I_{PP}		—	100	—	—	100	—	A	Peak radiation induced photo-current
di/dt		—	—	800	—	—	160	A/ μ sec	Rate of rise of photo-current
L_1		0.1	—	—	0.5	—	—	μH	Circuit inductance required to limit di/dt

Table 3. Single Event Effects ⑨

Parameter	Typical	Units	Ion	LET (Si) (MeV/mg/cm ²)	Range (μm)	V_{DS} Bias (V)	V_{GS} Bias (V)
V_{DS}	100	V	Ni	28	~41	100	-5

**Fig 1.** Typical Output Characteristics**Fig 2.** Typical Output Characteristics**Fig 3.** Typical Transfer Characteristics**Fig 4.** Normalized On-Resistance Vs. Temperature

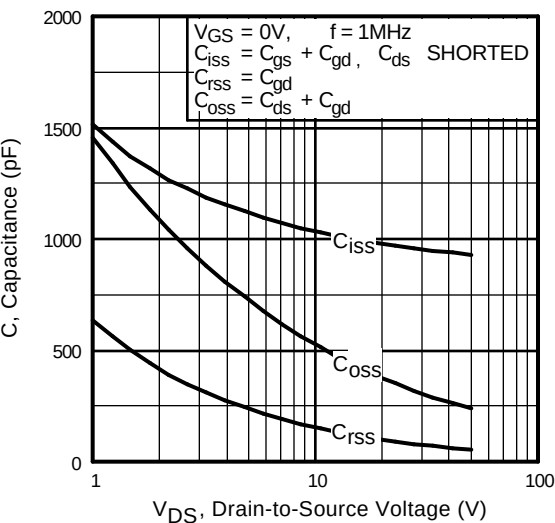


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

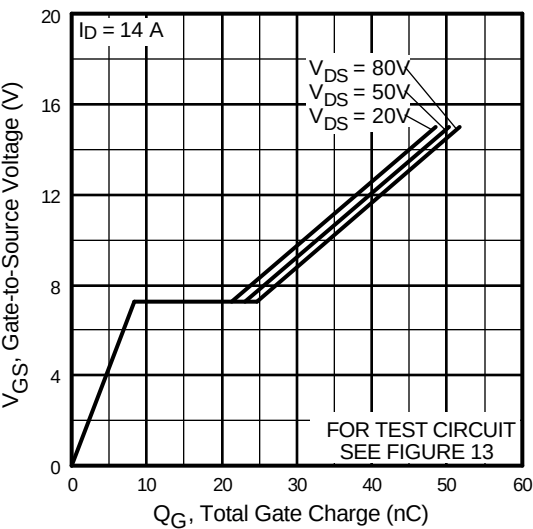


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

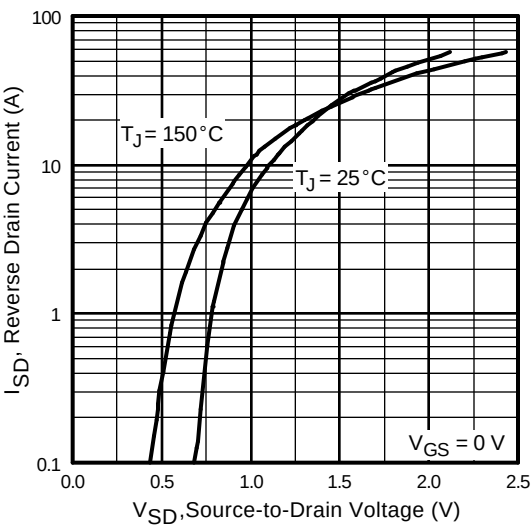


Fig 7. Typical Source-Drain Diode Forward Voltage

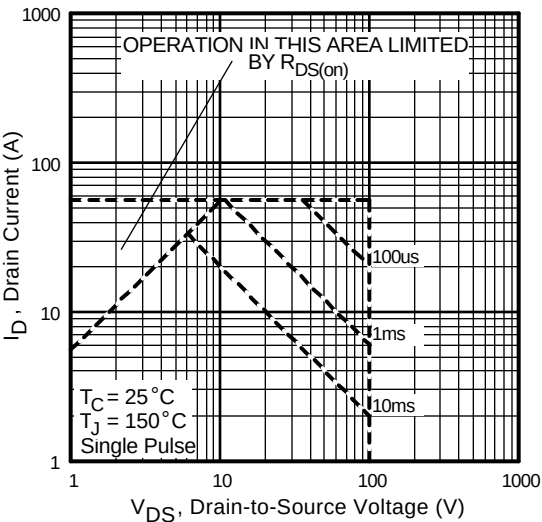


Fig 8. Maximum Safe Operating Area

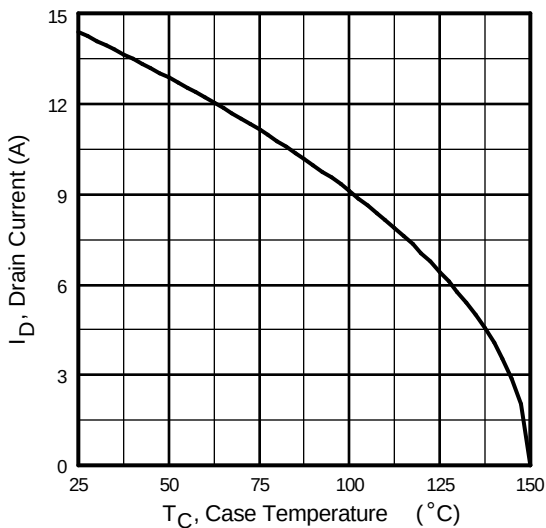


Fig 9. Maximum Drain Current Vs. Case Temperature

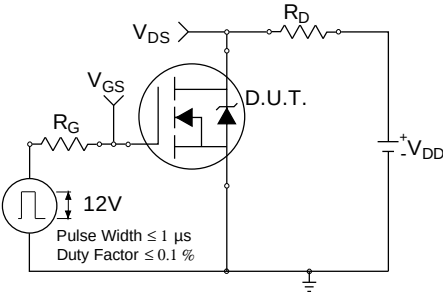


Fig 10a. Switching Time Test Circuit

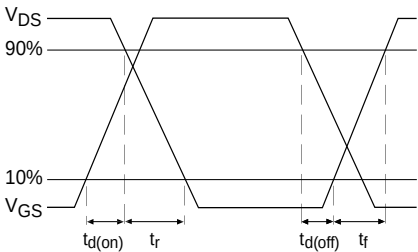


Fig 10b. Switching Time Waveforms

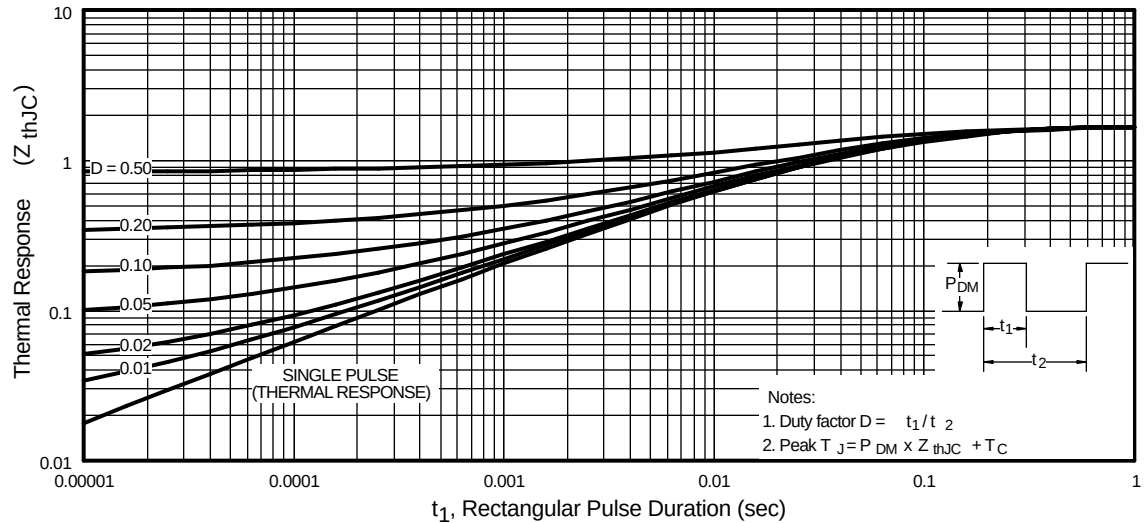


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

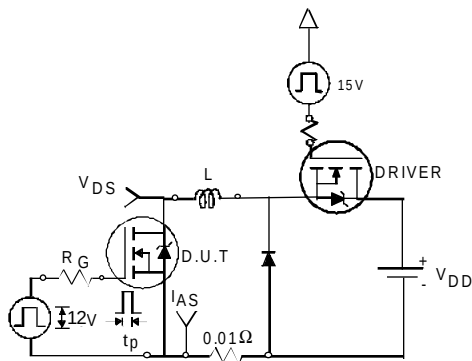


Fig 12a. Unclamped Inductive Test Circuit

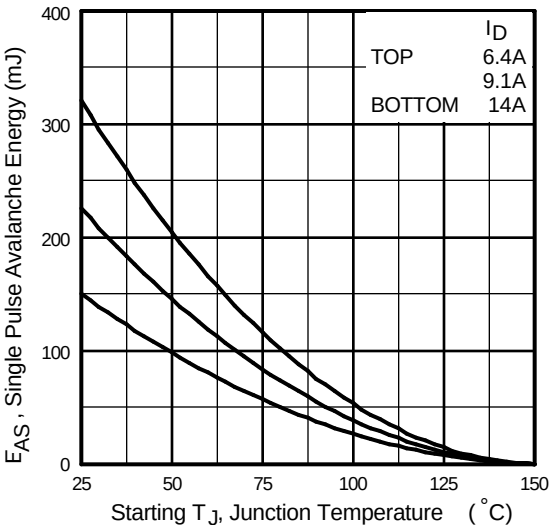


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

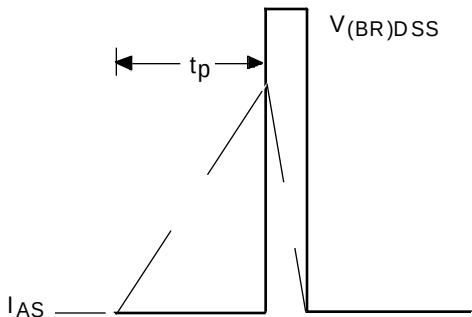


Fig 12b. Unclamped Inductive Waveforms

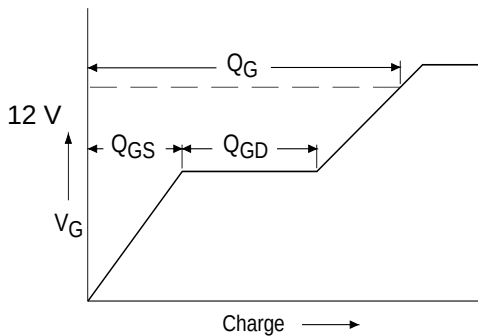


Fig 13a. Basic Gate Charge Waveform

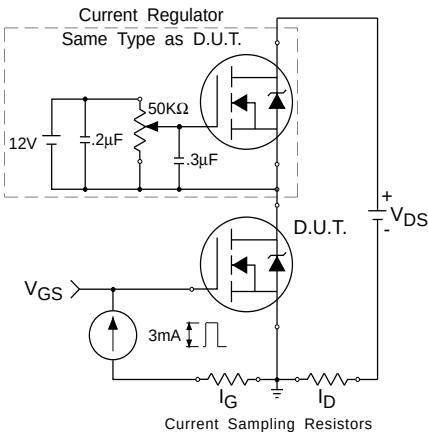
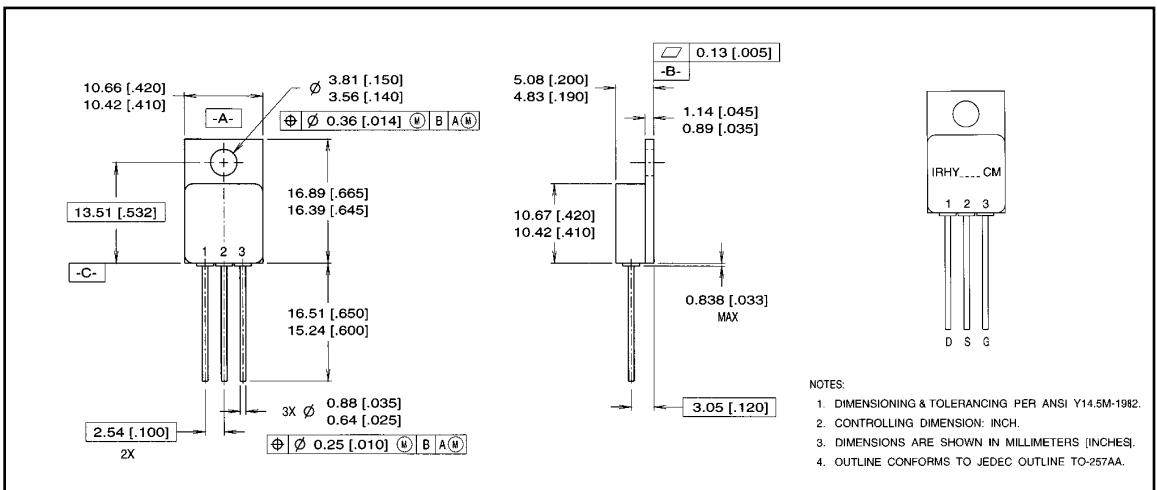


Fig 13b. Gate Charge Test Circuit

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
Refer to current HEXFET reliability report.
- ② $V_{DD} = 25V$, starting $T_J = 25^{\circ}C$, $E_{AS} = [0.5 * L * (I_L)^2]$
Peak $I_L = 14.4A$, $R_G = 25V$, $L = 1.4mH$
- ③ $I_{SD} \leq 14.4A$, $di/dt \leq 395A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^{\circ}C$
Suggested $R_G = 2.35\Omega$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^{\circ}C/W$
 $W/K = W/^{\circ}C$
- ⑥ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑦ **Total Dose Irradiation with V_{DS} Bias.**
 $V_{DS} = 0.8$ rated BV_{DSS} (pre-radiation) applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑧ This test is performed using a flash x-ray source operated in the e-beam mode (energy ~ 2.5 MeV), 30 nsec pulse.
- ⑨ Process characterized by independent laboratory.
- ⑩ All Pre-Radiation and Post-Radiation test conditions are **identical** to facilitate direct comparison for circuit applications.

Case Outline and Dimensions — TO 257AA



CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International IOR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

<http://www.irf.com/>

Data and specifications subject to change without notice.

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